

Transparent Layer of a LED Device and the Method for Growing the Same

ABSTRACT OF THE INVENTION

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A transparent layer of a LED device and the method for growing the same are disclosed in this present invention. This present invention provides an improved liquid phase epitaxy (LPE) process for growing a transparent layer of a LED device. In the above-mentioned 10 LPE process, an improved supersaturated solution is utilized to overcome the shortcomings in the prior art, wherein the supersaturated solution comprises antimony and/or indium as a solvent. Furthermore, a metallic zinc and/or magnesium dopant is added into the supersaturated solution to optimize the characters of 15 the transparent layer. Therefore, this invention can provide a more efficient method for growing a transparent layer of a LED device, and the quality of the above-mentioned transparent layer can thereby be improved.